

MG1275S-BA1MM




Features

- Ultra Low Loss
- High Ruggedness
- High Short Circuit Capability
- Positive Temperature Coefficient
- With Fast Free-Wheeling Diodes

Applications

- Inverter
- Converter
- Welder
- SMPS and UPS
- Induction Heating

Agency Approvals

| AGENCY | AGENCY FILE NUMBER |
|---|--------------------|
|  | E71639 |

Module Characteristics ($T_c = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Min | Typ | Max | Unit |
|------------|-------------------------------------|-------------------|-----|-----|-----|------|
| R_{thJC} | Junction-to-Case Thermal Resistance | Per IGBT | | | 0.2 | K/W |
| R_{thJD} | | Per Inverse Diode | | | 0.5 | K/W |
| Torque | Module-to-Sink | Recommended (M6) | 3 | | 5 | N-m |
| Torque | Module Electrodes | Recommended (M5) | 2.5 | | 5 | N-m |
| Weight | | | | 150 | | g |

Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Values | Unit |
|--------------|--------------------------------------|---|-------------|------------------|
| IGBT | | | | |
| V_{CES} | Collector - Emitter Voltage | | 1200 | V |
| V_{GES} | Gate - Emitter Voltage | | ± 20 | V |
| I_c | DC Collector Current | $T_c=25^\circ\text{C}$ | 105 | A |
| | | $T_c=80^\circ\text{C}$ | 75 | A |
| I_{cpuls} | Pulsed Collector Current | $T_c=25^\circ\text{C}, t_p=1\text{ms}$ | 210 | A |
| | | $T_c=80^\circ\text{C}, t_p=1\text{ms}$ | 150 | |
| P_{tot} | Power Dissipation Per IGBT | | 630 | W |
| T_J | Junction Temperature Range | | -40 to +150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature Range | | -40 to +125 | $^\circ\text{C}$ |
| V_{isol} | Insulation Test Voltage | AC, t=1min | 3000 | V |
| Diode | | | | |
| V_{RRM} | Repetitive Reverse Voltage | | 1200 | V |
| $I_{F(AV)}$ | Average Forward Current | $T_c=25^\circ\text{C}$ | 90 | A |
| | | $T_c=80^\circ\text{C}$ | 60 | A |
| $I_{F(RMS)}$ | RMS Forward Current | | 90 | A |
| I_{FSM} | Non-Repetitive Surge Forward Current | $T_J=45^\circ\text{C}, t=10\text{ms}, \text{Sine}$ | 430 | A |
| | | $T_J=45^\circ\text{C}, t=8.3\text{ms}, \text{Sine}$ | 450 | |

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

MG1275S-BA1MM

Electrical and Thermal Specifications ($T_c = 25^\circ\text{C}$, unless otherwise specified)

| Symbol | Parameters | Test Conditions | Min | Typ | Max | Unit | |
|---------------|--|---|-------------------------|------|------|---------------|----|
| IGBT | | | | | | | |
| $V_{GE(th)}$ | Gate - Emitter Threshold Voltage | $V_{CE}=V_{GE}, I_C=3\text{mA}$ | 5.0 | 6.2 | 7.0 | V | |
| $V_{CE(sat)}$ | Collector - Emitter Saturation Voltage | $I_C=75\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$ | | 1.8 | | V | |
| | | $I_C=75\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$ | | 2.0 | | V | |
| I_{CES} | Collector Leakage Current | $V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$ | | 0.2 | 0.5 | mA | |
| | | $V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$ | | 2 | | mA | |
| I_{GES} | Gate Leakage Current | $V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}$ | -100 | | 100 | nA | |
| Q_{ge} | Gate Charge | $V_{CC}=600\text{V}, I_C=75\text{A}, V_{GE}=\pm 15\text{V}$ | | 780 | | nC | |
| C_{ies} | Input Capacitance | $V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$ | | 5.52 | | nF | |
| C_{oes} | Output Capacitance | | | 0.4 | | | |
| C_{res} | Reverse Transfer Capacitance | | | 0.26 | | | |
| $t_{d(on)}$ | Turn - on Delay Time | $V_{CC}=600\text{V}$ $I_C=75\text{A}$ $R_G=15\Omega$ $V_{GE}=\pm 15\text{V}$ Inductive Load | $T_J=25^\circ\text{C}$ | | 150 | | ns |
| | | | $T_J=125^\circ\text{C}$ | | 160 | | ns |
| t_r | Rise Time | | $T_J=25^\circ\text{C}$ | | 65 | | ns |
| | | | $T_J=125^\circ\text{C}$ | | 65 | | ns |
| $t_{d(off)}$ | Turn - off Delay Time | | $T_J=25^\circ\text{C}$ | | 440 | | ns |
| | | | $T_J=125^\circ\text{C}$ | | 500 | | ns |
| t_f | Fall Time | | $T_J=25^\circ\text{C}$ | | 55 | | ns |
| | | | $T_J=125^\circ\text{C}$ | | 70 | | ns |
| E_{on} | Turn - on Energy | | $T_J=25^\circ\text{C}$ | | 7.45 | | mJ |
| | | | $T_J=125^\circ\text{C}$ | | 10.3 | | mJ |
| E_{off} | Turn - off Energy | $T_J=25^\circ\text{C}$ | | 4.9 | | mJ | |
| | | $T_J=125^\circ\text{C}$ | | 7.8 | | mJ | |
| Diode | | | | | | | |
| V_F | Forward Voltage | $I_F=75\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$ | | 2.0 | 2.48 | V | |
| | | $I_F=75\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$ | | 1.7 | 2.2 | V | |
| t_{rr} | Reverse Recovery Time | $I_F=75\text{A}, V_R=800\text{V}$ $di_F/dt=-1000\text{A}/\mu\text{s}$ $T_J=125^\circ\text{C}$ | | 200 | | ns | |
| I_{RRM} | Max. Reverse Recovery Current | | | 70 | | A | |
| Q_{rr} | Reverse Recovery Charge | | | 8.2 | | μC | |

Figure 1: Typical Output Characteristics

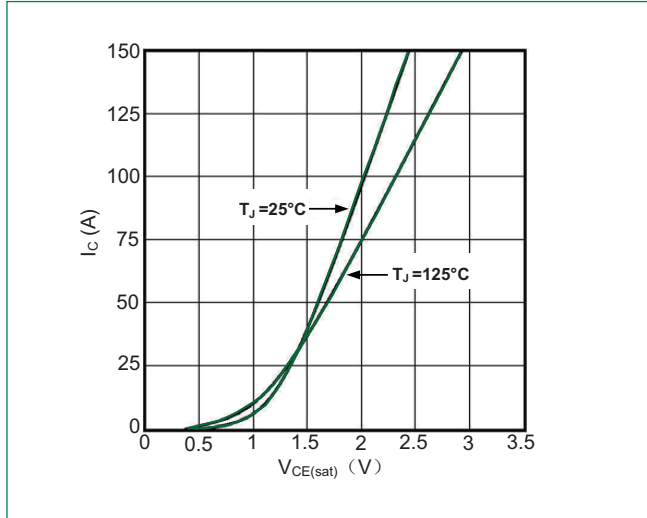


Figure 2: Typical Transfer characteristics

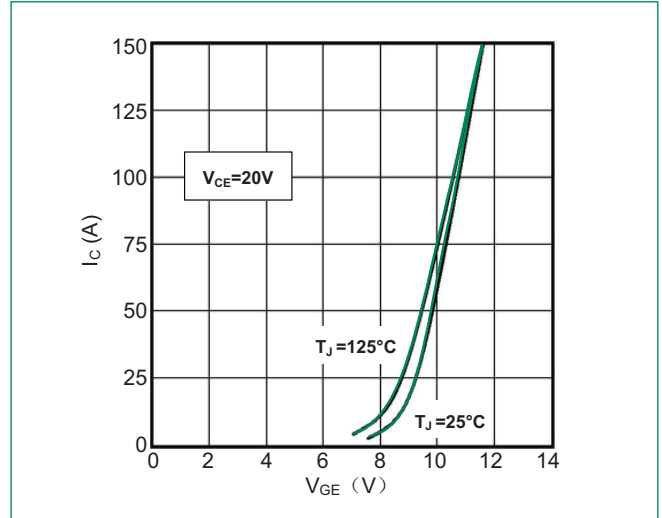


Figure 3: Switching Energy vs. Collector Current

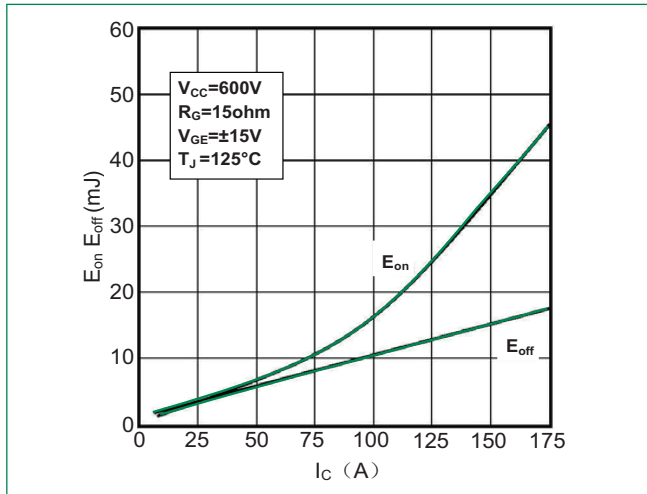


Figure 4: Switching Energy vs. Gate Resistor

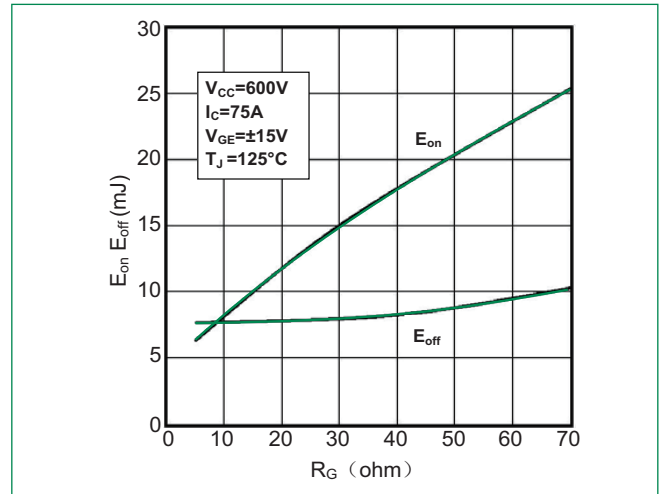


Figure 5: Switching Times vs. Collector Current

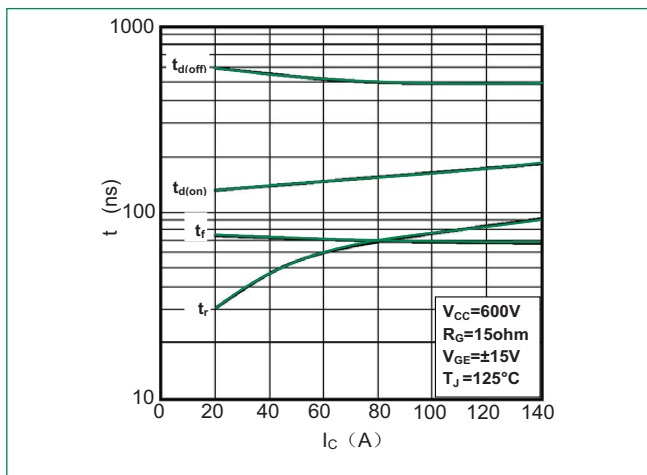


Figure 6: Switching Times vs. Gate Resistor

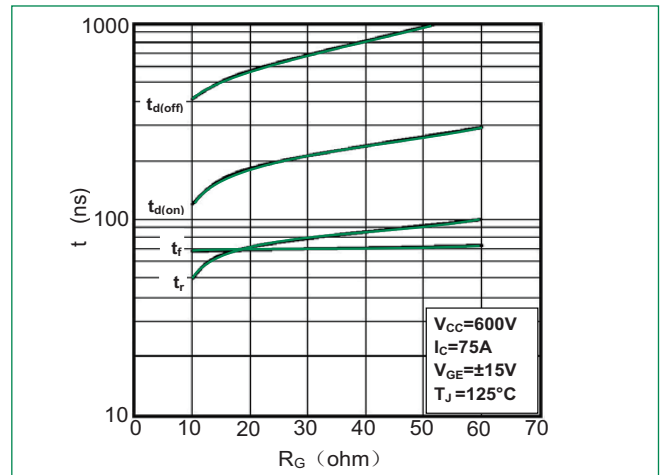


Figure 7: Gate Charge characteristics

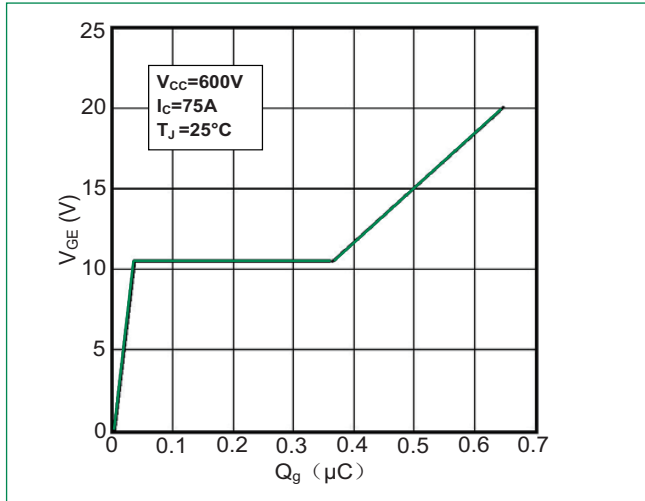


Figure 8: Typical Capacitances vs. V_{CE}

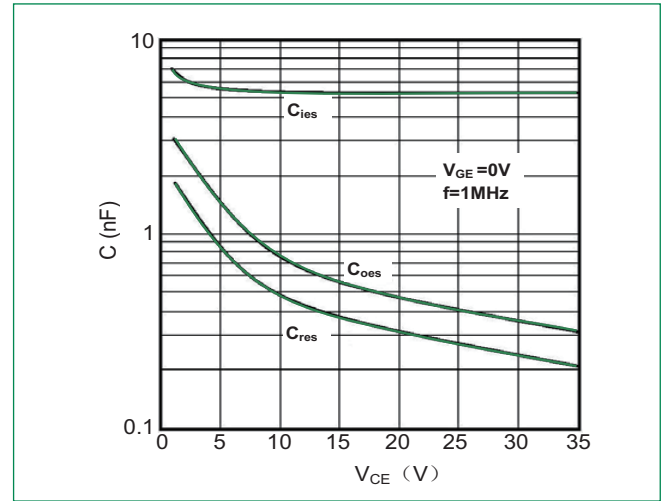


Figure 9: Reverse Biased Safe Operating Area

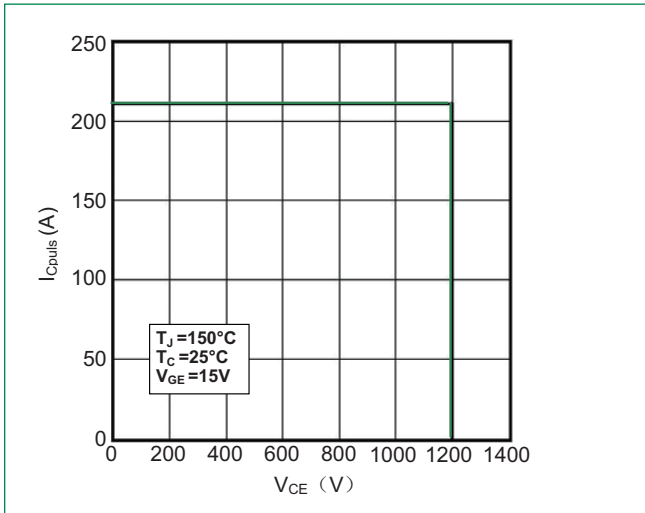


Figure 10: Short Circuit Safe Operating Area

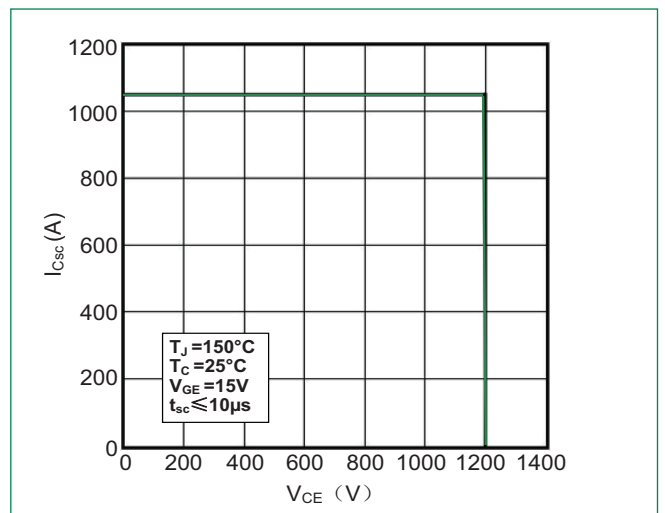


Figure 11: Rated Current vs. T_c

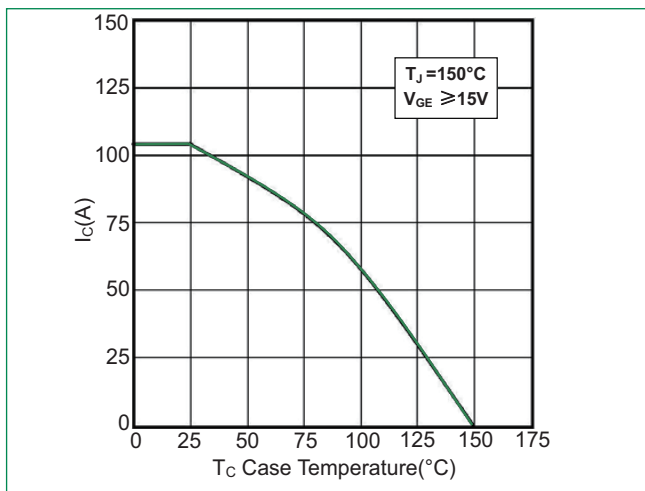


Figure 12: Diode Forward Characteristics

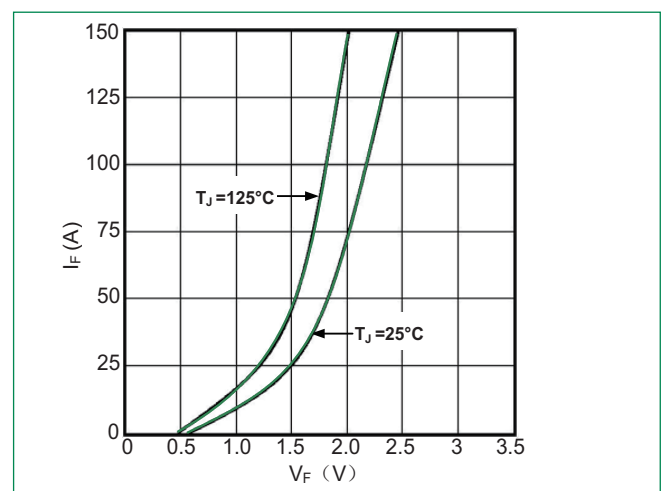


Figure 13: Transient Thermal Impedance of IGBT

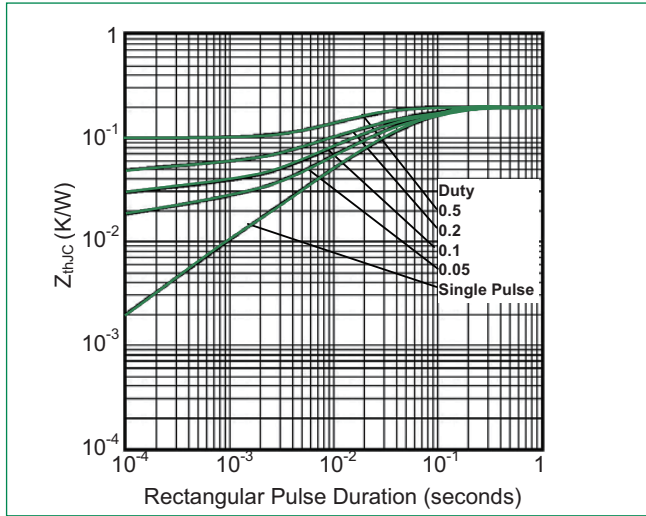
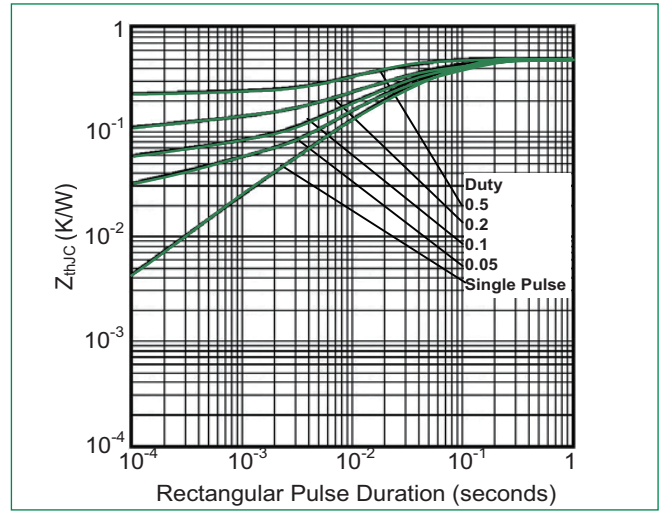
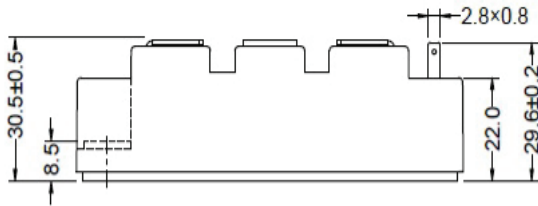


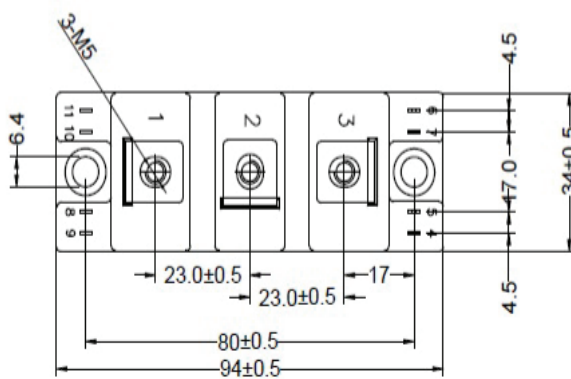
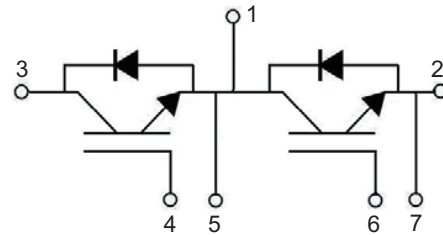
Figure 14: Transient Thermal Impedance of Diode



Dimensions-Package S



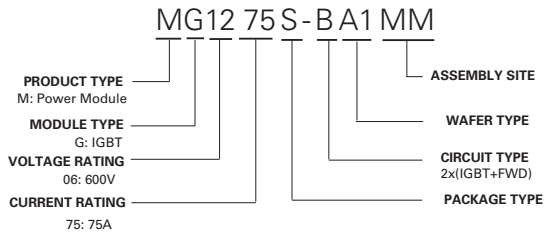
Circuit Diagram



Packing Options

| Part Number | Marking | Weight | Packing Mode | M.O.Q |
|---------------|---------------|--------|--------------|-------|
| MG1275S-BA1MM | MG1275S-BA1MM | 150g | Bulk Pack | 100 |

Part Numbering System



Part Marking System

